IN THE CLAIMS:

1 - 9 (Canceled)

10. (Original) A laser CVD device comprising:

a plasma unit for turning pretreating gas into a plasma state in atmosphere via arc discharge and supplying a plasma gas to a substrate, wherein said plasma unit includes a plasma generating chamber, a gas inlet for receiving pretreating gas to the plasma generating chamber, and an electrode for causing the pretreating gas to generate arc discharge, and a metal net for preventing the arc discharge from being effected on the substrate.;

means for radiating a laser beam to a deposition area on the substrate;

means for supplying film forming gas to the deposition area; and

means for sealing the film forming gas isolated from an external atmosphere, wherein

the deposition area of said substrate is pretreated by said plasma unit supplying the plasma gas to the substrate prior to a film formed by CVD over said deposition area of said substrate by activating the film forming gas by said laser beam.

11. (New) A laser CVD device comprising:

a plasma unit for turning pretreating gas into a plasma state and supplying a plasma gas to a substrate, wherein the pretreating gas is air;

wherein said plasma unit makes the plasma state by arc discharge;

wherein said plasma unit includes a plasma generating chamber, a gas inlet for receiving pretreating gas to the plasma generating chamber, and an electrode for causing the pretreating gas to generate arc discharge;

wherein said plasma unit further includes a metal net for preventing the arc discharge from being effected on the substrate;

means for radiating a laser beam to a deposition area on the substrate;

means for supplying film forming gas to the deposition area; and

means for sealing the film forming gas isolated from an external atmosphere, wherein

the deposition area of said substrate is pretreated by said plasma unit supplying the plasma gas to the substrate prior to a film formed by CVD over said deposition area of said substrate by activating the film forming gas by said laser beam.